



PROTON-ELECTROTEX RUSSIA

Optimum power handling
Low on-state and switching losses
Designed for traction and industrial applications

Rectifier Stud Diode Type D171-500X-12

Mean on-state current				I_{FAV}	500 A		
Repetitive peak reverse voltage				V_{RRM}	600...1200V		
V_{RRM} , V	600	700	800	900	1000	1100	1200
Voltage code	6	7	8	9	10	11	12
$T_{j\prime}$, °C	-60...+190						

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Maximum allowable average forward current	A	500 659	T _c =142 °C; T _c =120 °C; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	785	T _c =142 °C; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	16.0 19.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V;
			17.0 20.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	1200 1800	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V;
			1100 1600	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V;
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	600...1200	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz;	
V _{RSM}	Non-repetitive peak reverse voltages	V	700...1400	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; single pulse;	
V _R	Reverse continuous voltages	V	0.6·V _{RRM}	T _j =T _{j max} ;	
THERMAL					
T _{stg}	Storage temperature	°C	−60...+50		
T _j	Operating junction temperature	°C	−60...+190		
MECHANICAL					
M	Tightening torque	Nm	25...35		
a	Acceleration	m/s ²	100		

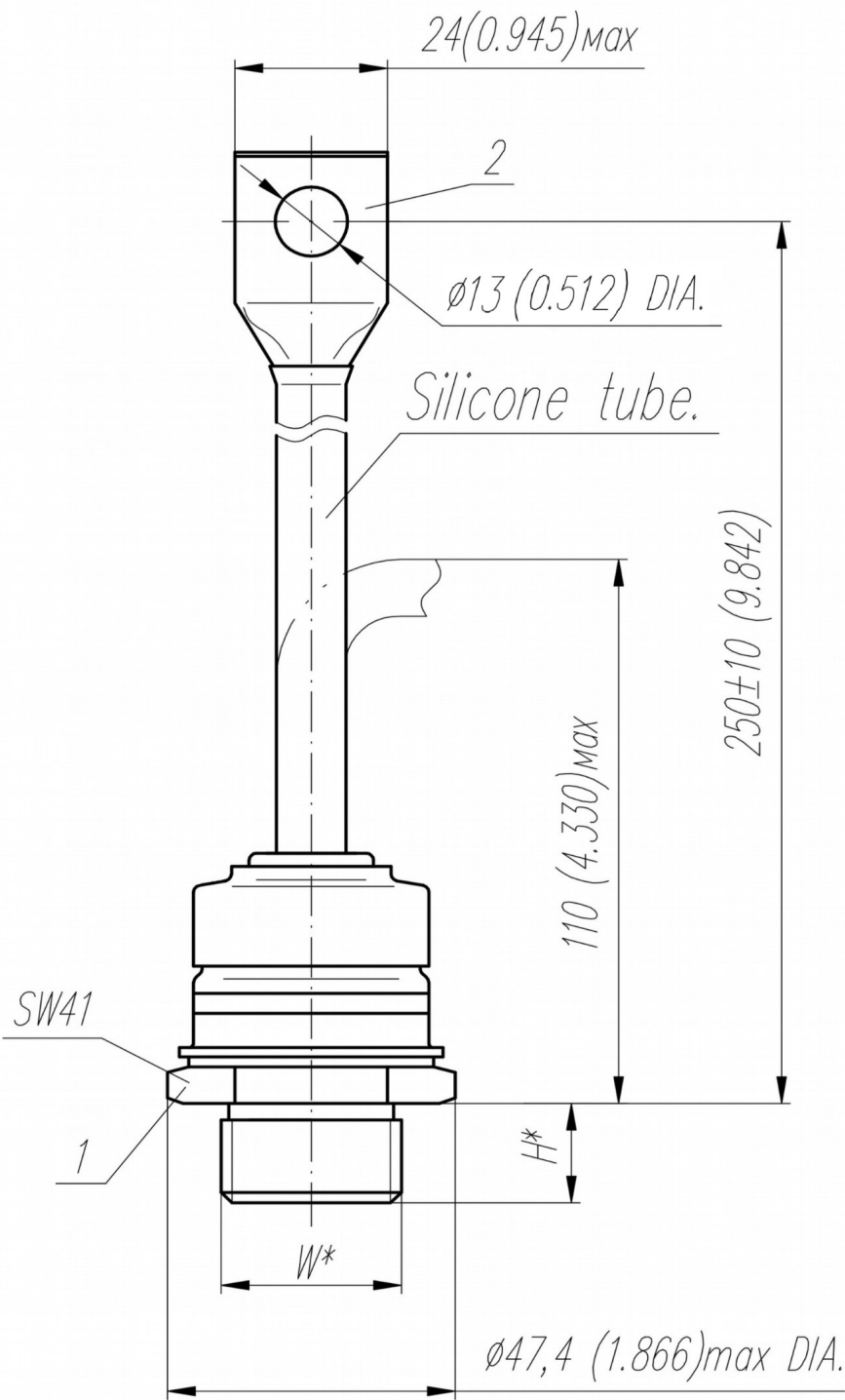
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	1.40	T _j =25 °C; I _{FM} =1570 A
V _{F(TO)}	Forward threshold voltage, max	V	0.809	T _j =T _{j max} ;
r _T	Forward slope resistance, max	mΩ	0.376	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	40	T _j =T _{j max} ; V _R =V _{RRM}
SWITCHING				
Q _r	Recovered charge, max	μC	830	T _j =T _{j max} ; I _{TM} =500 A ; di _R /dt=-10 A/μs ; V _R =100 V;
t _{rr}	Reverse recovery time, max	μs	15	
I _{rr}	Reverse recovery current, max	A	110	
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.075	Direct current
MECHANICAL				
m	Weight, max	g	410	
D _s	Surface creepage distance	mm (inch)	12.4 (4.882)	
D _a	Air strike distance	mm (inch)	12.4 (4.882)	

PART NUMBERING GUIDE

D	171	500	X	12	N
1	2	3	4	5	6

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Polarity: X – Cathode to Stud; Anode to Stud – no symbol
5. Voltage code
6. Ambient conditions: N – normal; T – tropical



Type of screw	W	H
Metric Screw Type C	M24x1,5 – 8g	19

Polarity		Example of code designation	Reference designation	Colors	
				Anode	Cathode
Reverse	Cathode to stud	D171-500X-12	∇	Black tube	-

All dimensions in millimeters (inches)

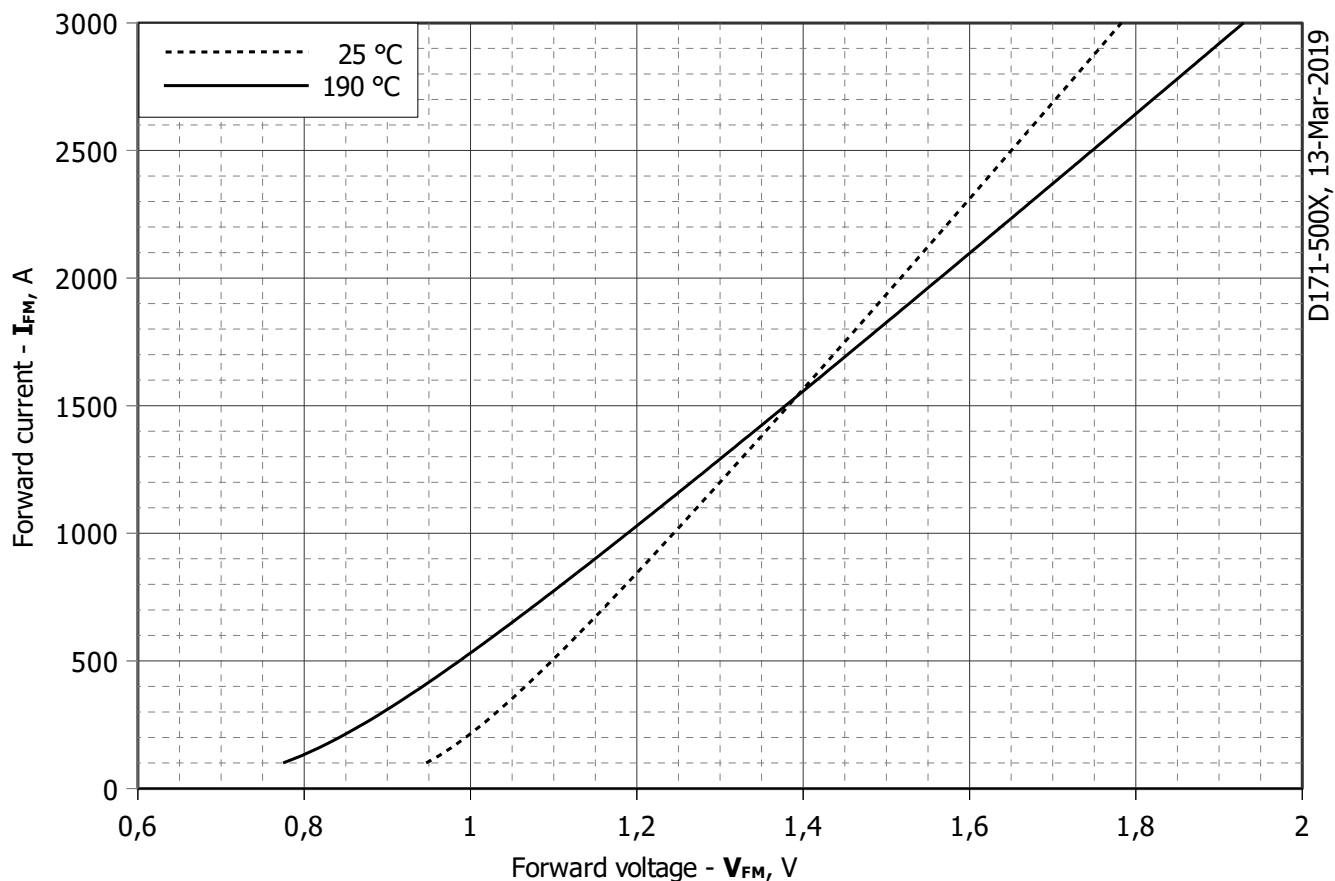


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\text{ max}}$
A	0.75818000	0.49236000
B	0.00026115	0.00036297
C	0.03751000	0.05786700
D	-0.00108460	-0.00210100

Forward characteristic model (see Fig. 1).

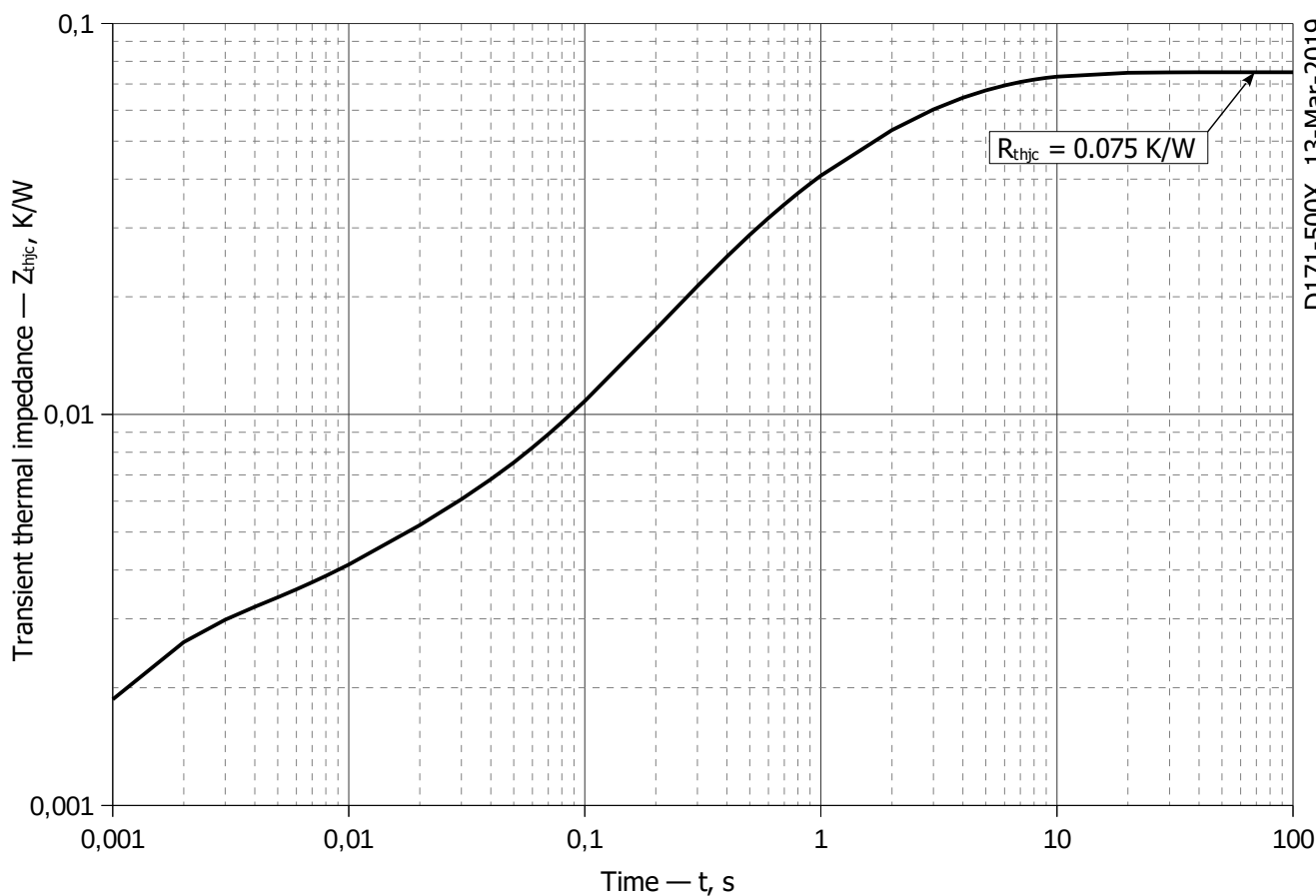


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC

i	1	2	3	4	5	6
R_i , K/W	0.013357	0.02733	0.01495	0.001445	0.002488	0.01543
τ_i , s	4.627	2.249	0.3406	0.01043	0.0009112	0.9081

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

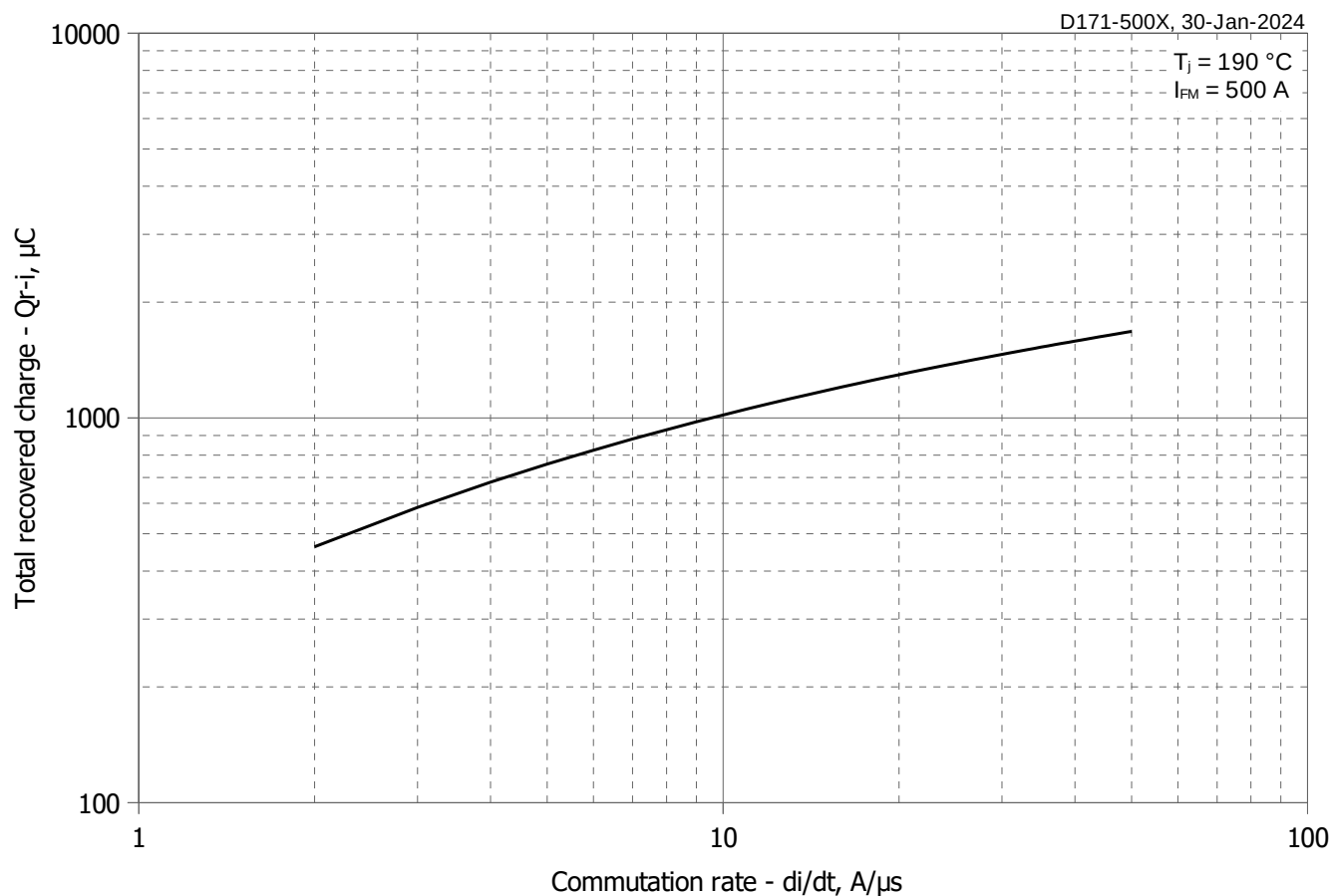


Fig 3 – Maximum recovered charge Q_{r-i} (integral) vs. commutation rate di_R/dt

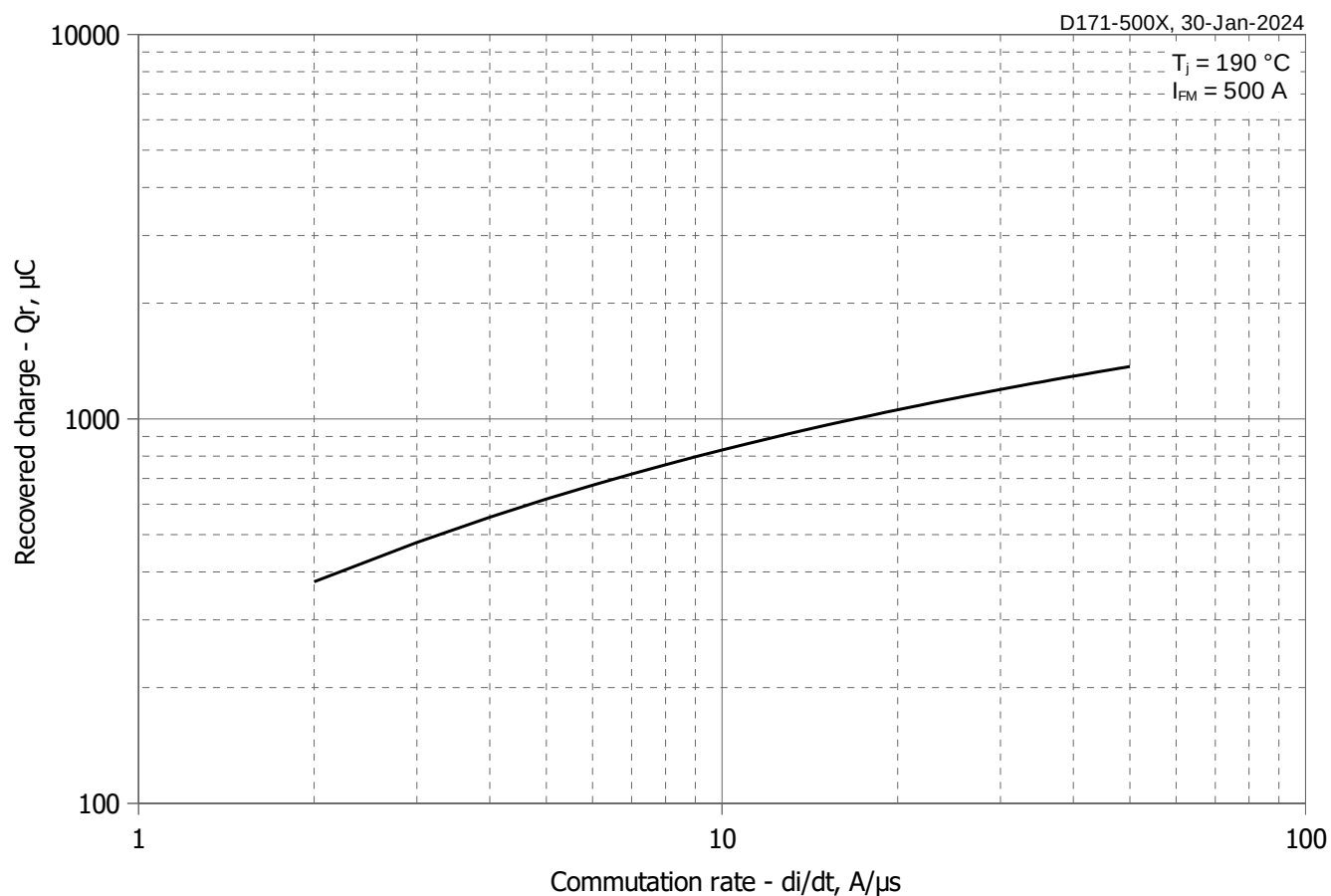


Fig 4 – Maximum recovered charge Q_r vs. commutation rate di_R/dt (25% chord)

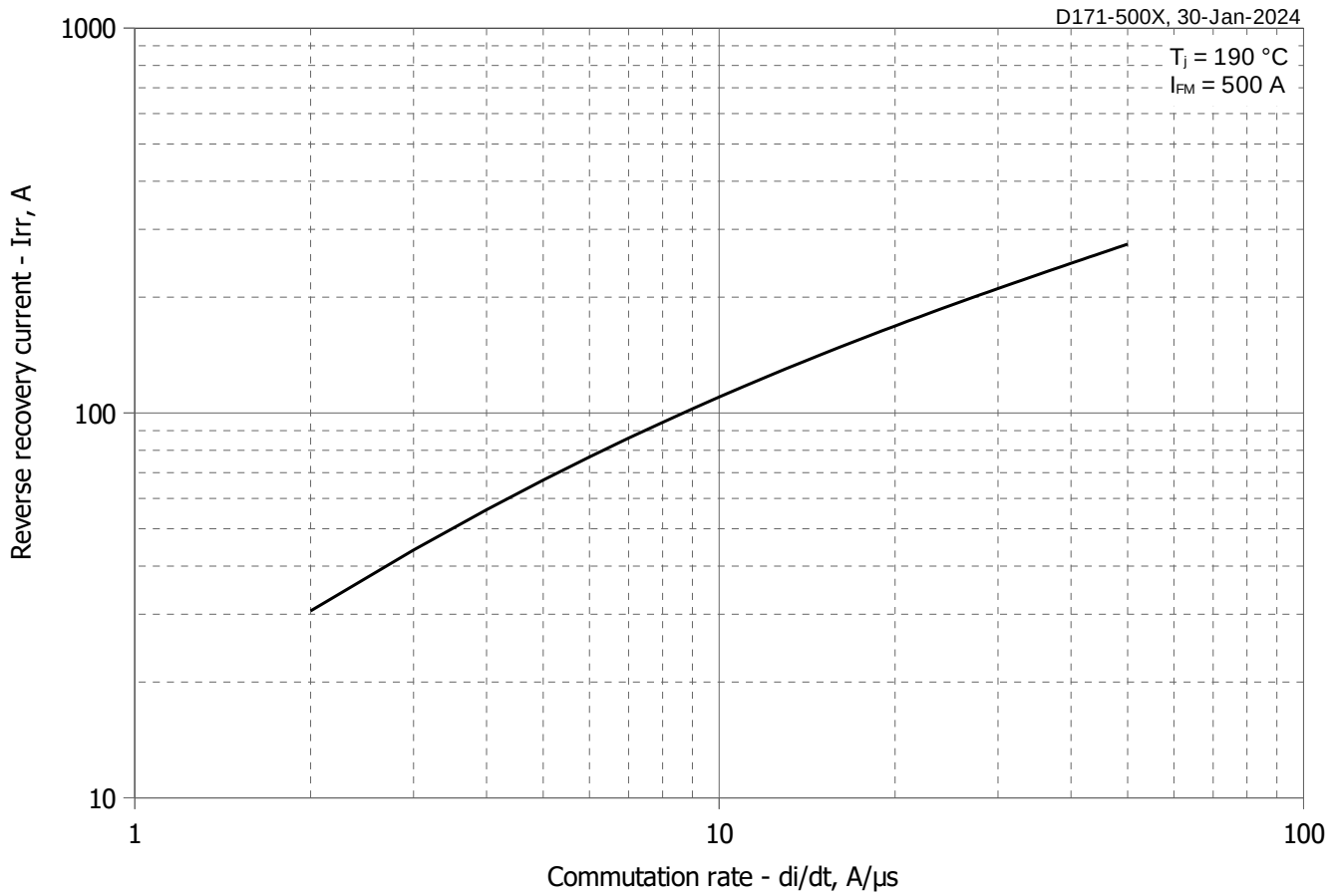


Fig 5 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

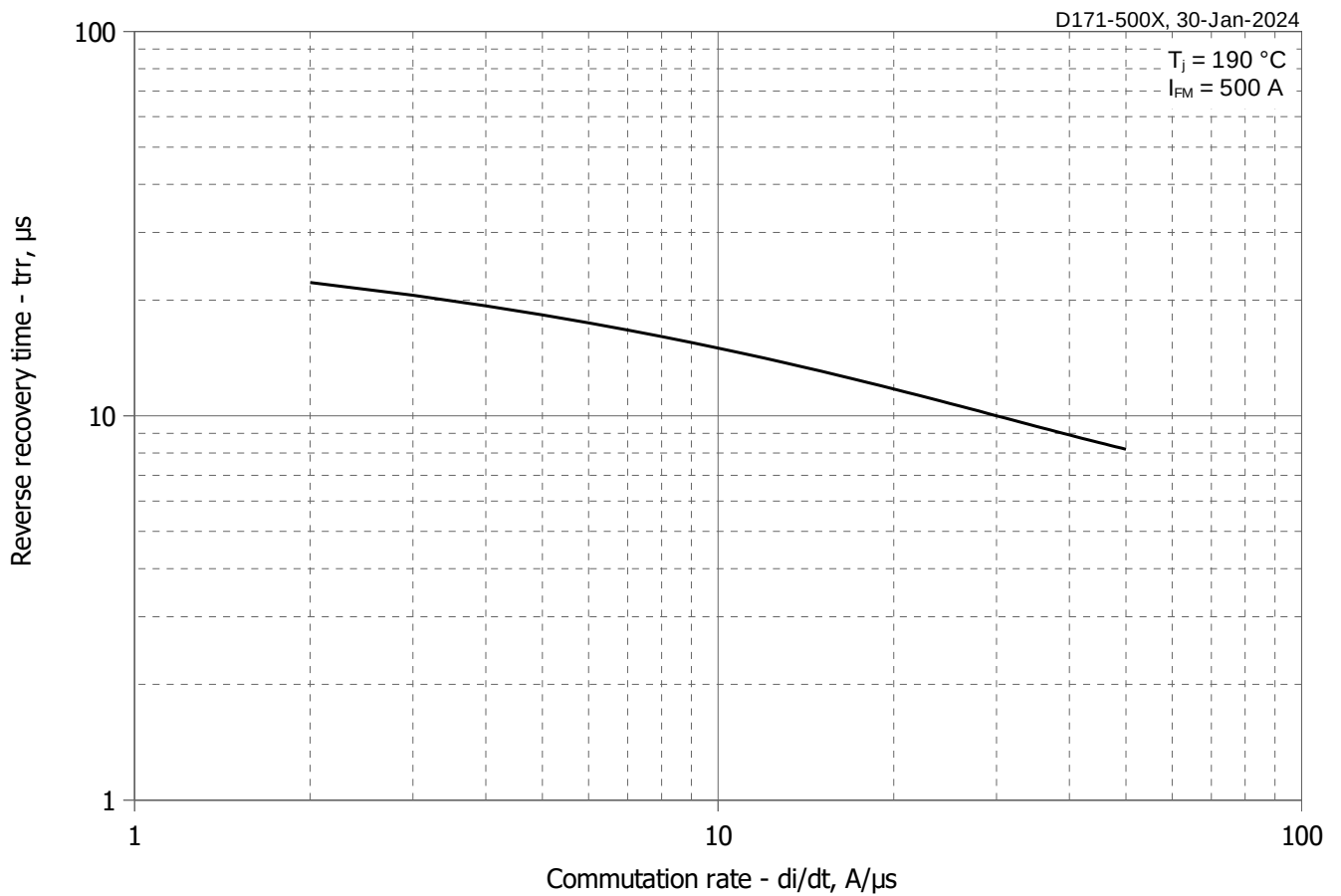
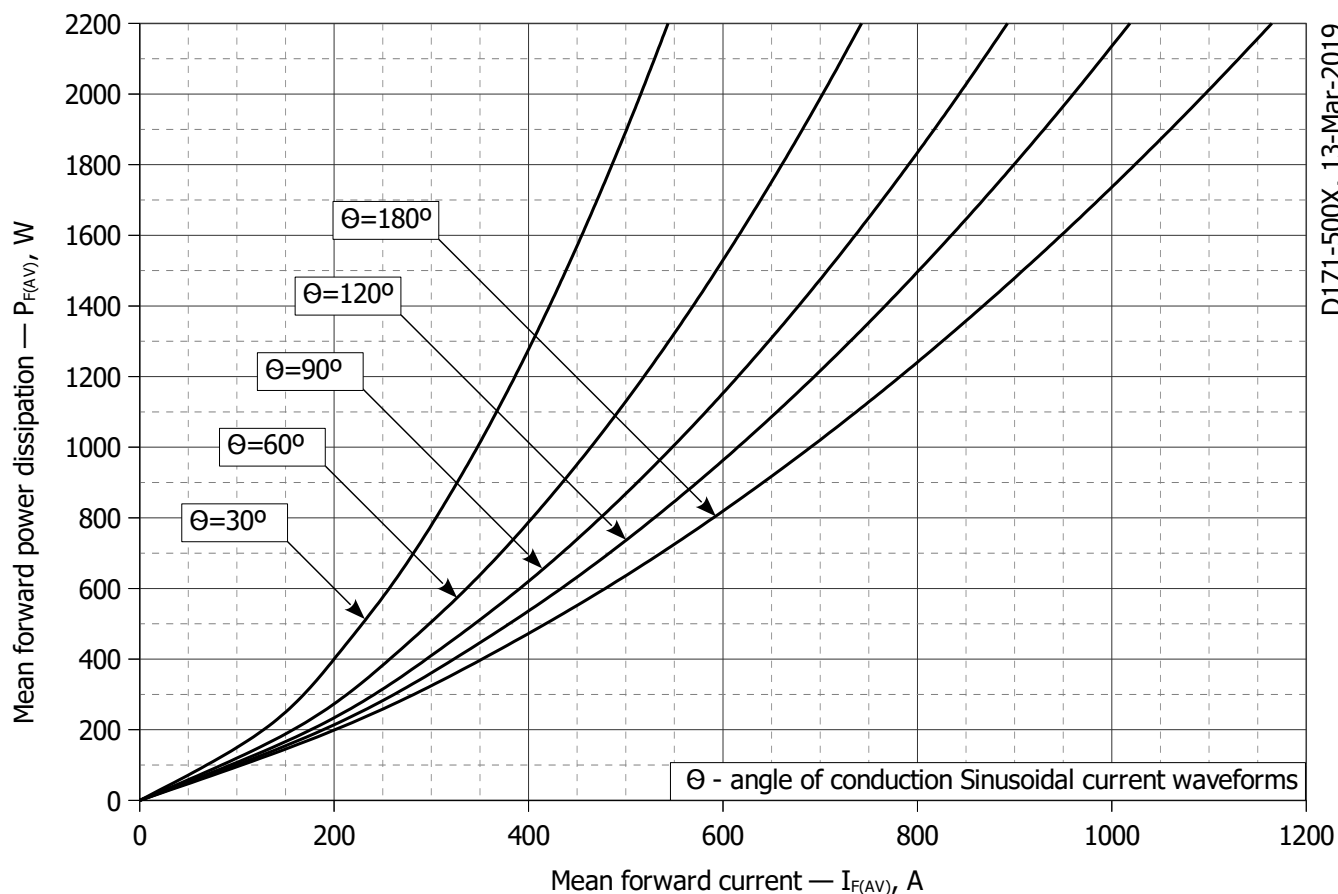
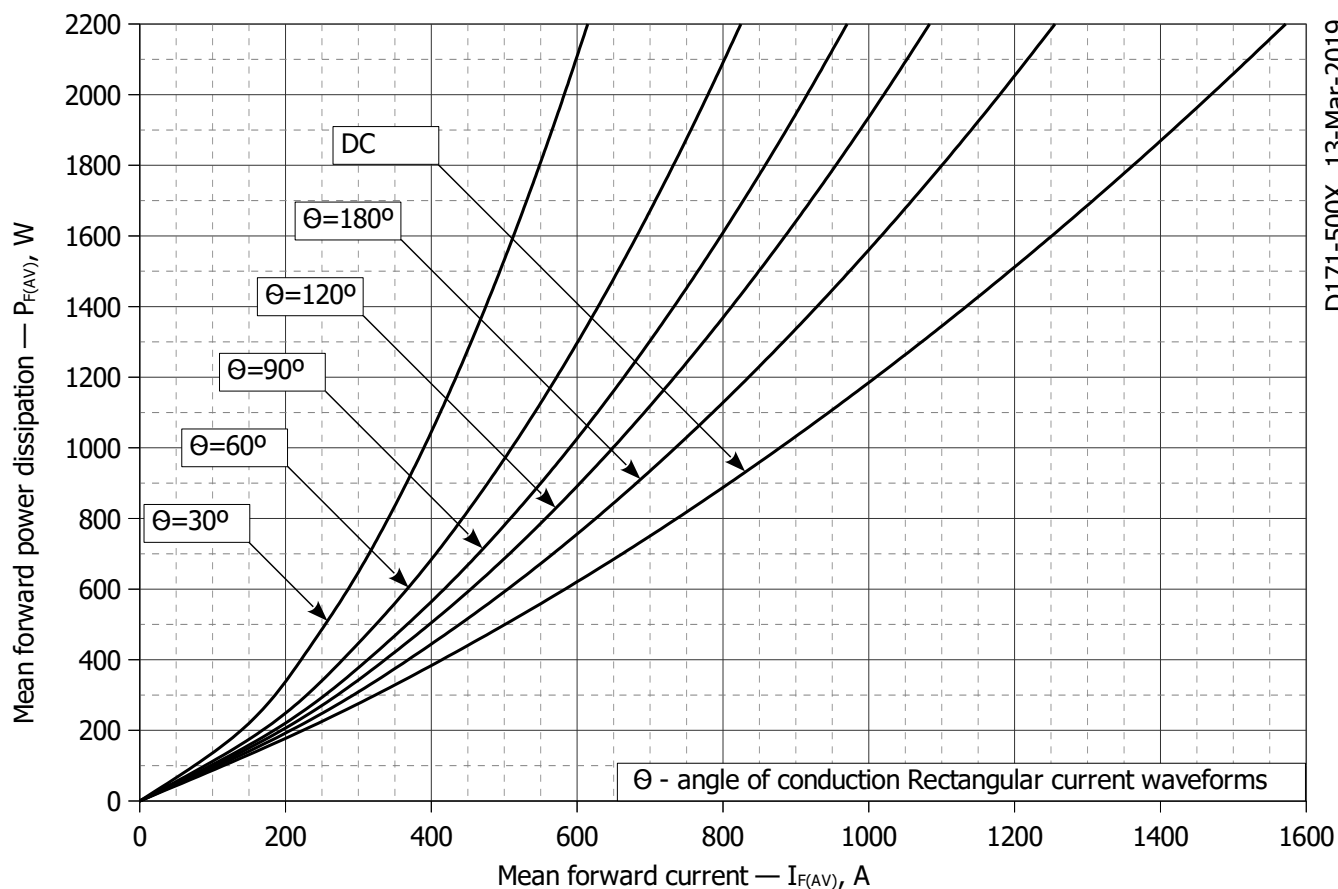


Fig 6 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)



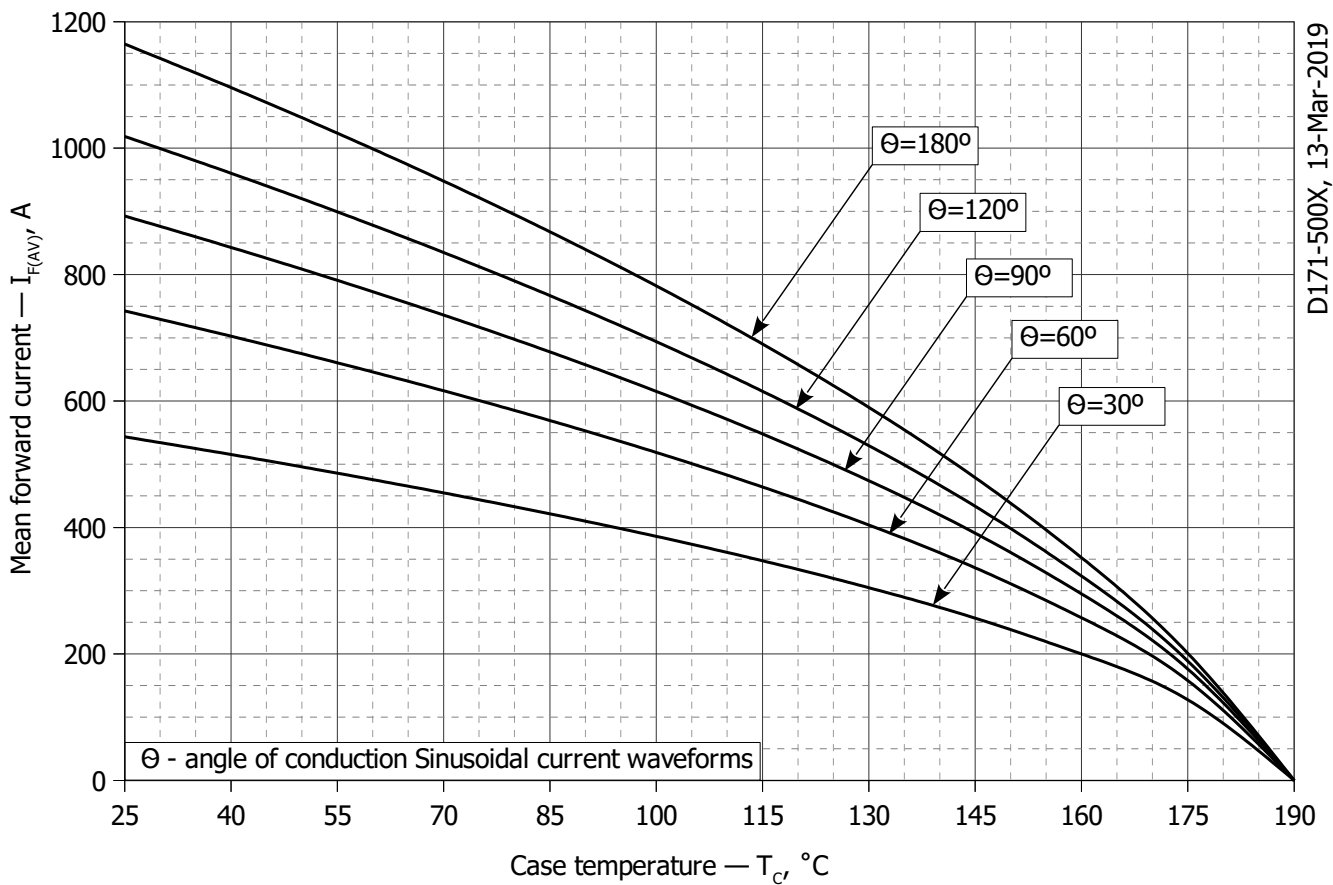
D171-500X, 13-Mar-2019

Fig. 7 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)



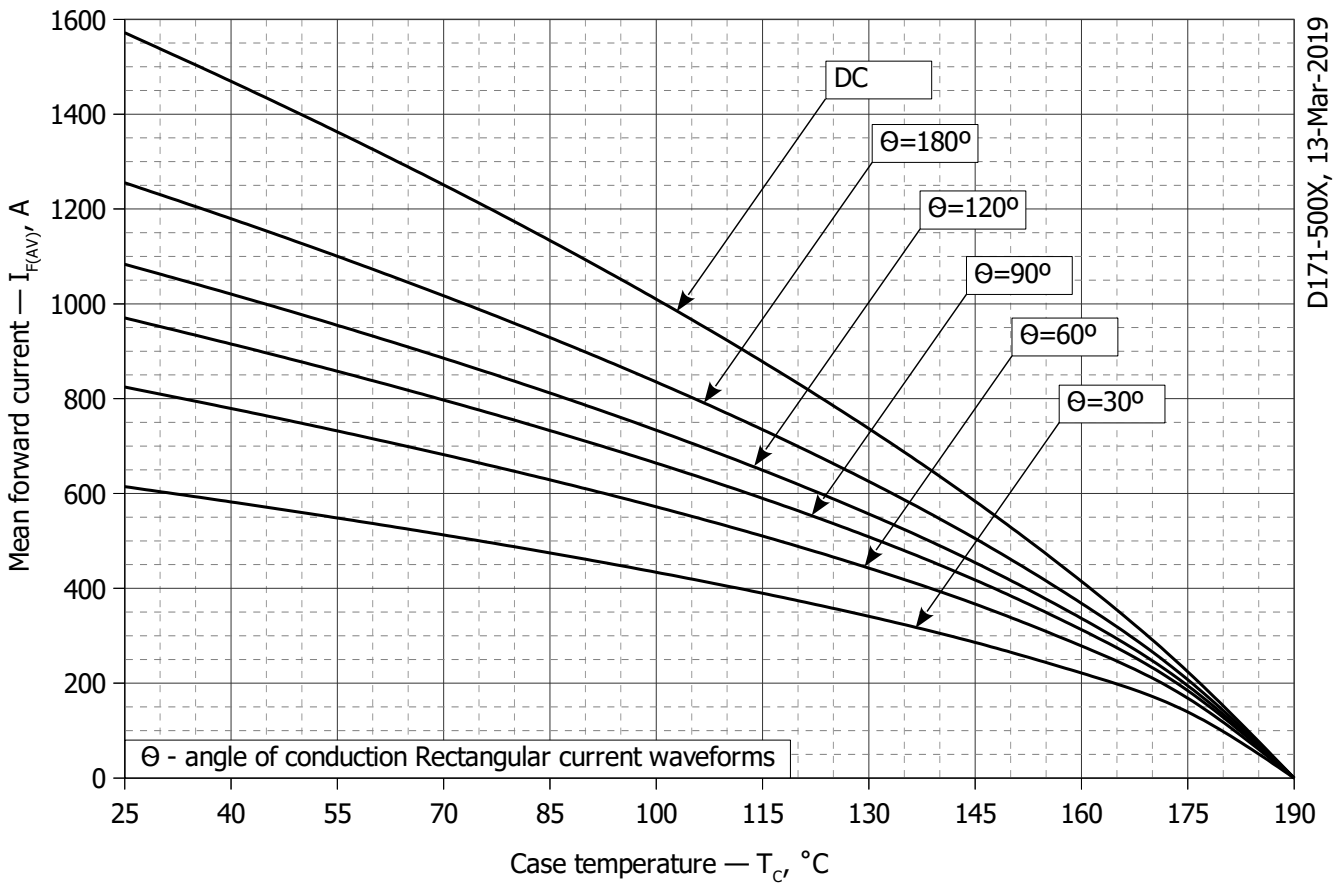
D171-500X, 13-Mar-2019

Fig. 8 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)



D171-500X, 13-Mar-2019

Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)



D171-500X, 13-Mar-2019

Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

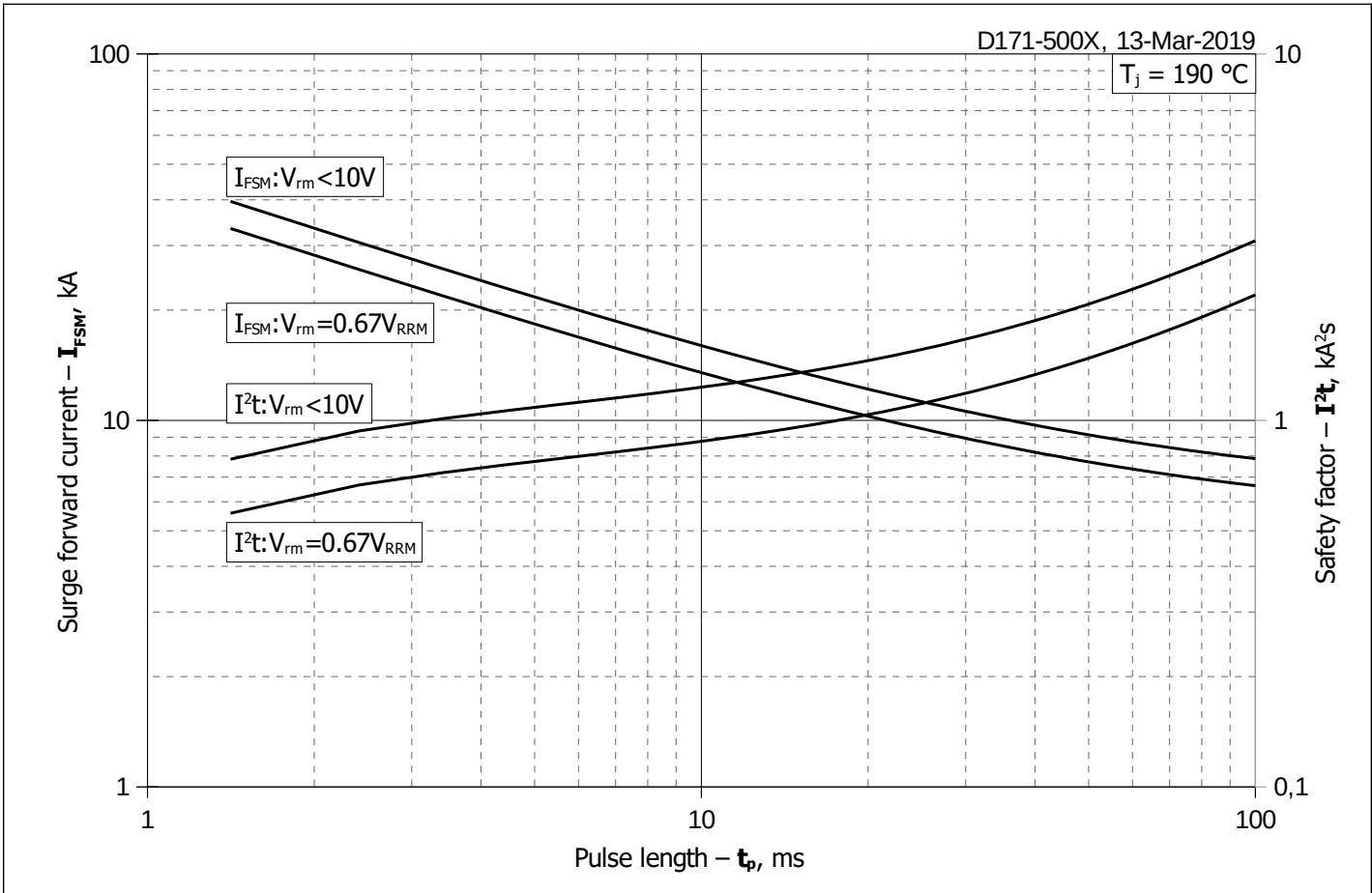


Fig. 11 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

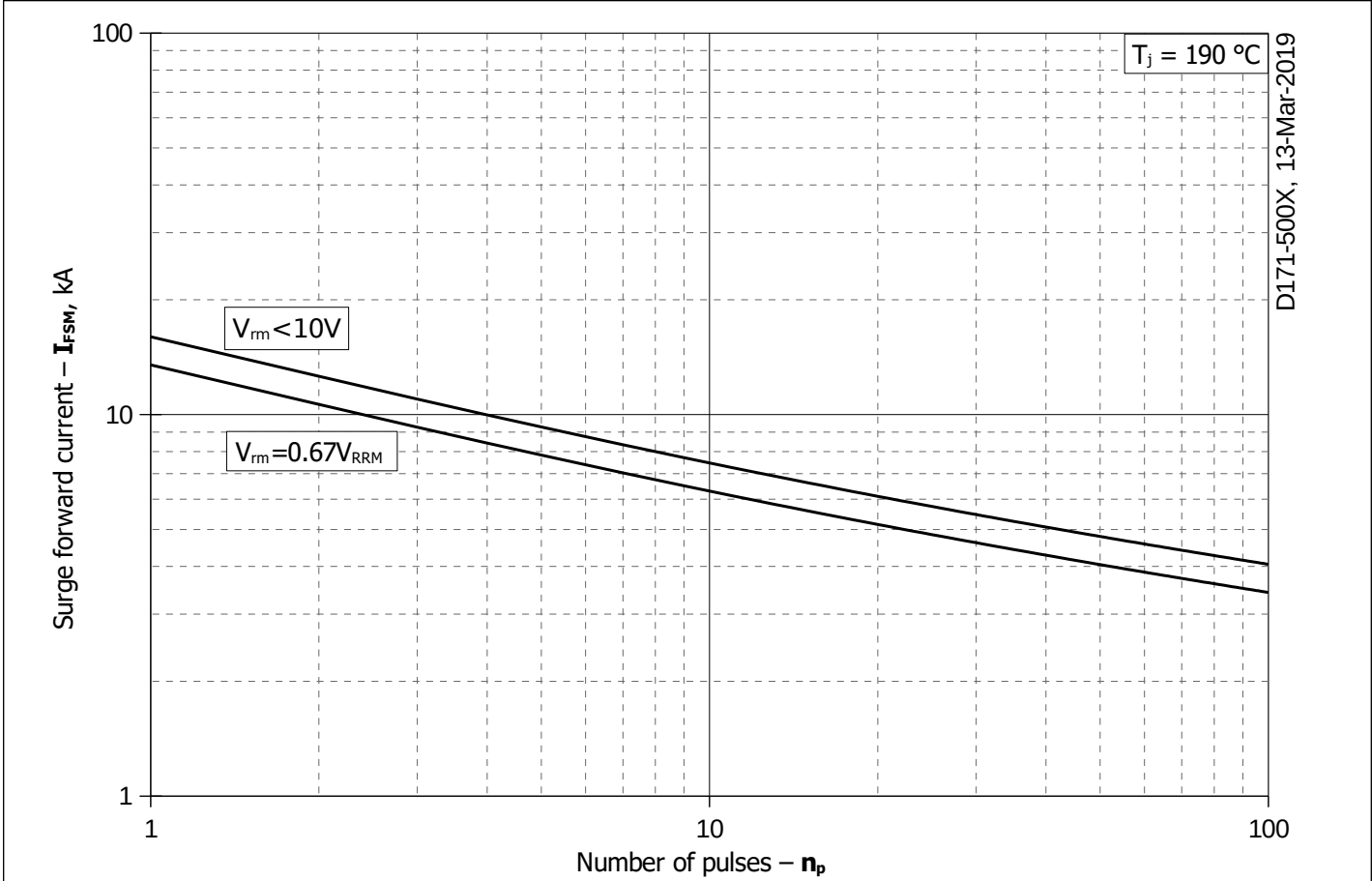


Fig. 12 - Maximum surge forward current I_{FSM} vs. number of pulses n_p